

# IRF3315PbF

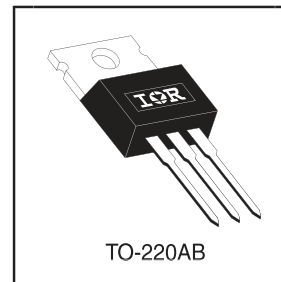
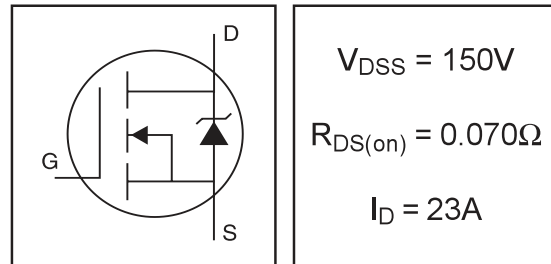
HEXFET® Power MOSFET

- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

## Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	23	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	16	
$I_{DM}$	Pulsed Drain Current ①	84	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	94	W
	Linear Derating Factor	0.63	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy②	350	mJ
$I_{AR}$	Avalanche Current③	12	A
$E_{AR}$	Repetitive Avalanche Energy④	9.4	mJ
dv/dt	Peak Diode Recovery dv/dt ⑤	2.5	V/ns
$T_J$	Operating Junction and Storage Temperature Range	-55 to + 175	
$T_{STG}$			
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

## Thermal Resistance

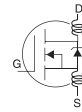
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	1.6	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	---	
$R_{\theta JA}$	Junction-to-Ambient	---	62	

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International  
**IR** Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.187	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.070	$\Omega$	$V_{GS} = 10V, I_D = 12A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	17	—	—	S	$V_{DS} = 50V, I_D = 12A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 150V, V_{GS} = 0V$ $V_{DS} = 120V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -20V$
$Q_g$	Total Gate Charge	—	—	95	nC	$I_D = 12A$ $V_{DS} = 120V$ $V_{GS} = 10V$ , See Fig. 6 and 13 ④
$Q_{gs}$	Gate-to-Source Charge	—	—	11		
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	47		
$t_{d(on)}$	Turn-On Delay Time	—	9.6	—	ns	$V_{DD} = 75V$ $I_D = 12A$ $R_G = 5.1\Omega$ $R_D = 5.9\Omega$ , See Fig. 10 ④
$t_r$	Rise Time	—	32	—		
$t_{d(off)}$	Turn-Off Delay Time	—	49	—		
$t_f$	Fall Time	—	38	—		
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	1300	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$ , See Fig. 5
$C_{oss}$	Output Capacitance	—	300	—		
$C_{riss}$	Reverse Transfer Capacitance	—	160	—		

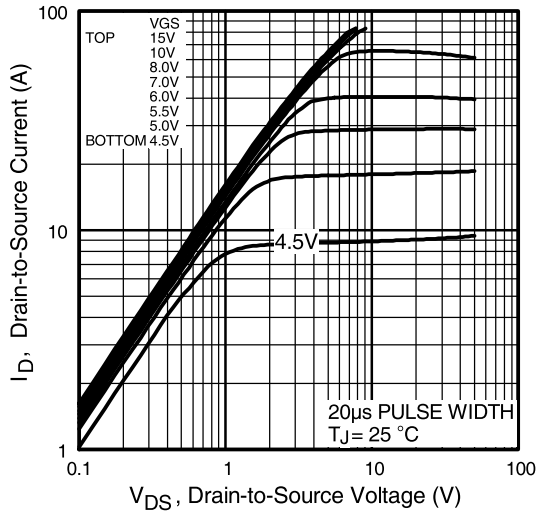


## Source-Drain Ratings and Characteristics

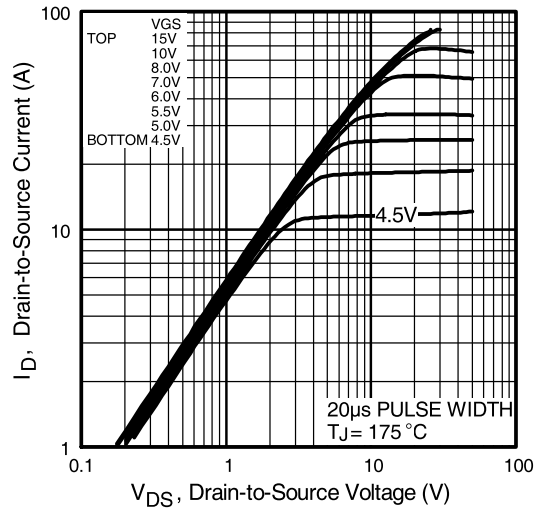
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	23	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	84		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 12A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	174	260	ns	$T_J = 25^\circ\text{C}, I_F = 12A$
$Q_{rr}$	Reverse Recovery Charge	—	1.2	1.7	$\mu\text{C}$	$di/dt = 100A/\mu\text{s}$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

### Notes:

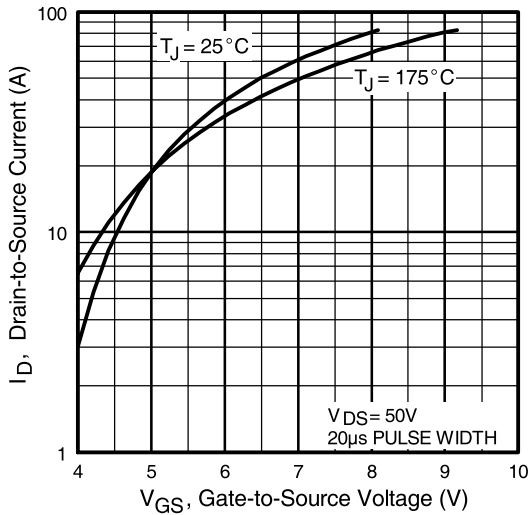
- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 4.9\text{mH}$   
 $R_G = 25\Omega, I_{AS} = 12A$ . (See Figure 12)
- ③  $I_{SD} \leq 12A, di/dt \leq 140A/\mu\text{s}, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .



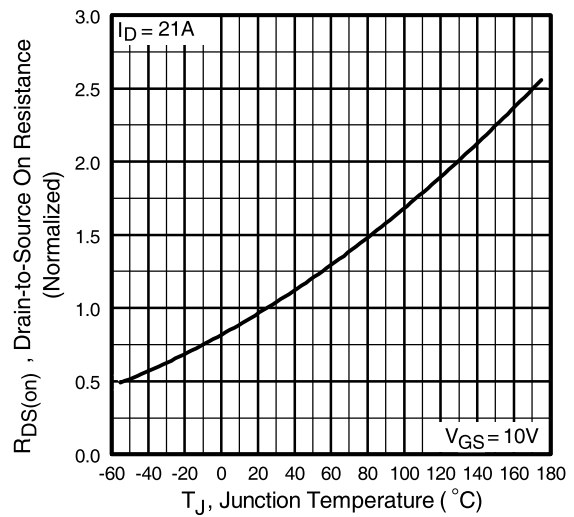
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

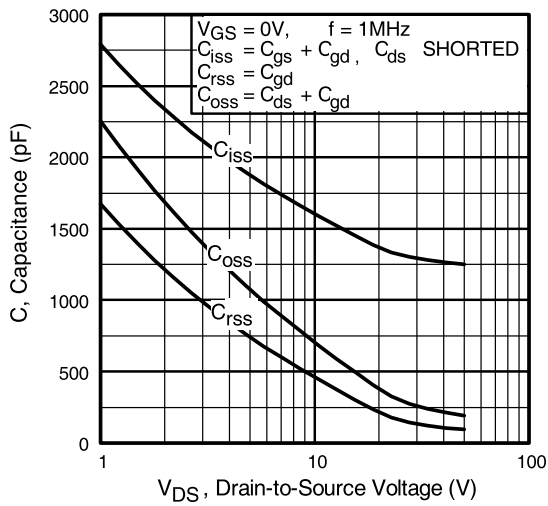


**Fig 3.** Typical Transfer Characteristics

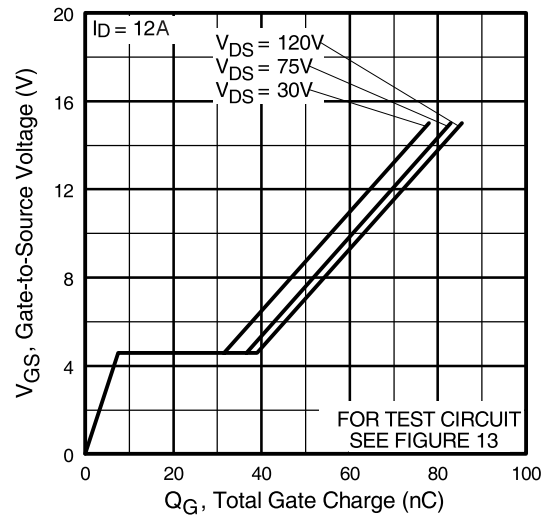


**Fig 4.** Normalized On-Resistance Vs. Temperature

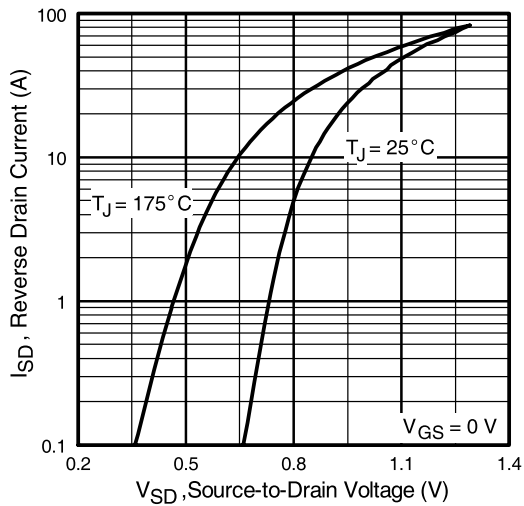
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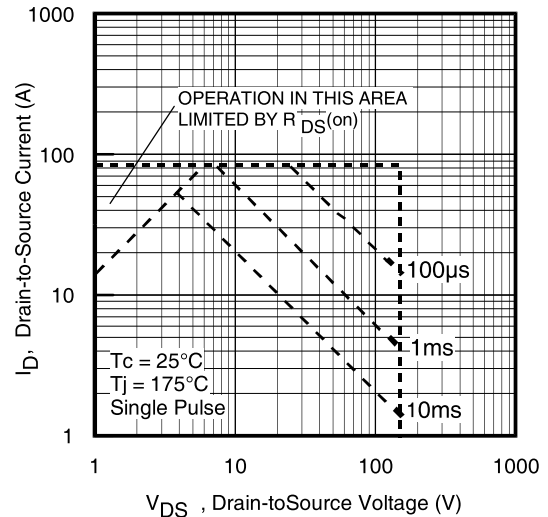
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



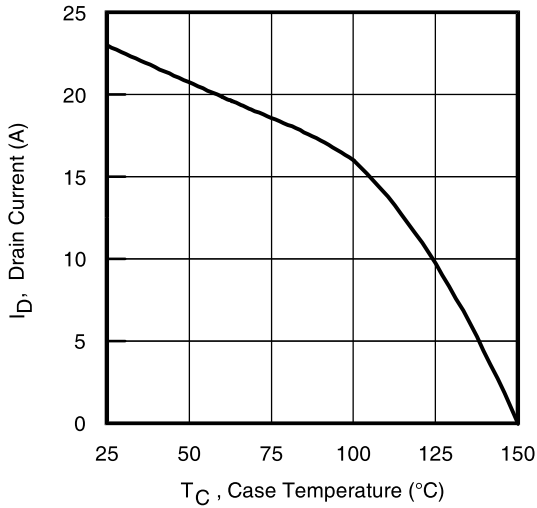
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



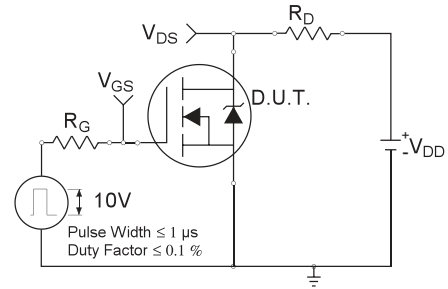
**Fig 7.** Typical Source-Drain Diode Forward Voltage



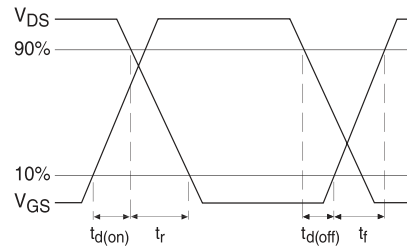
**Fig 8.** Maximum Safe Operating Area



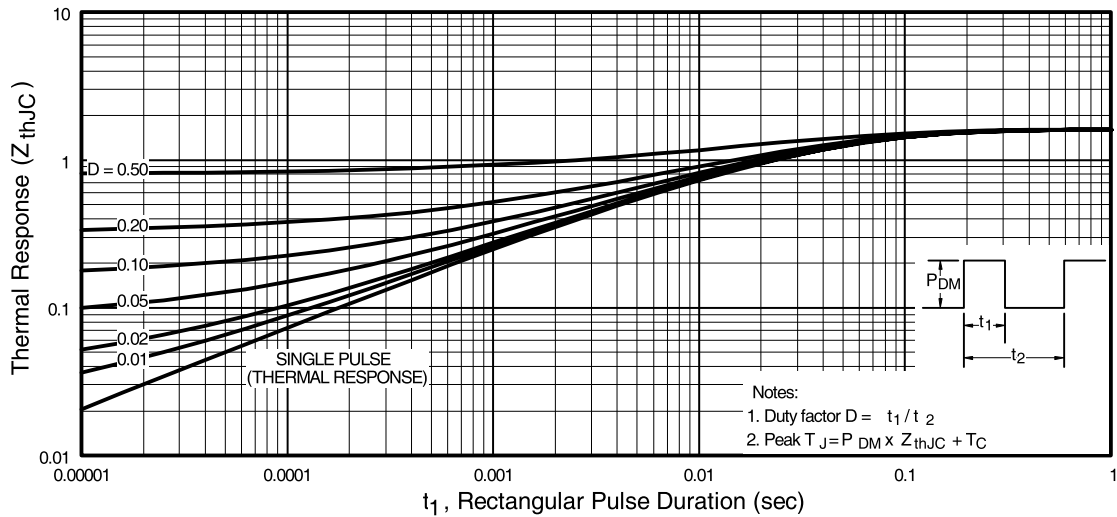
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



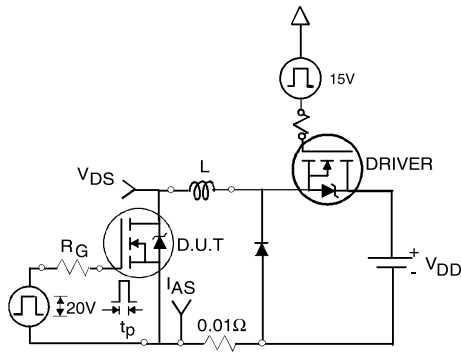
**Fig 10b.** Switching Time Waveforms



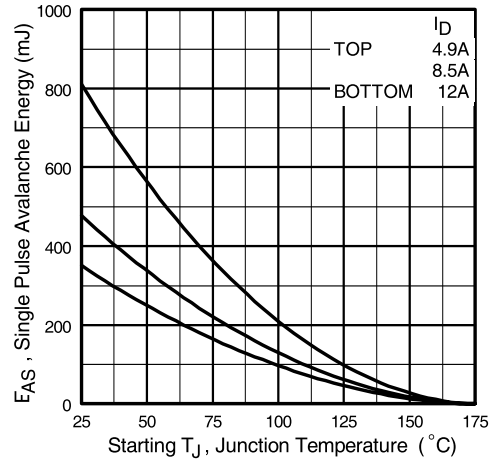
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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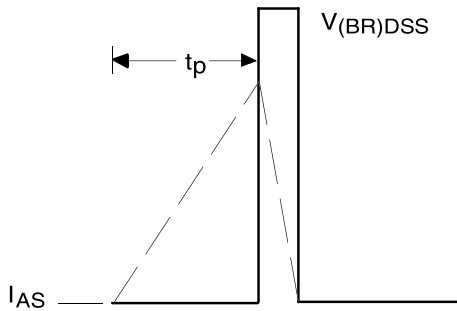
International  
**IR** Rectifier



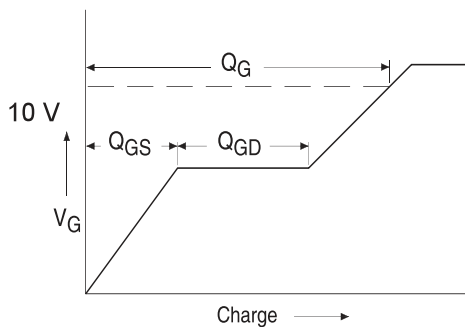
**Fig 12a.** Unclamped Inductive Test Circuit



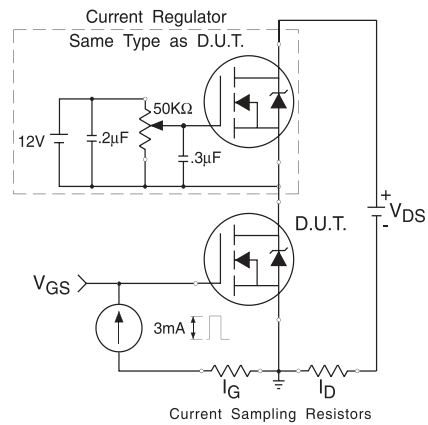
**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 12b.** Unclamped Inductive Waveforms

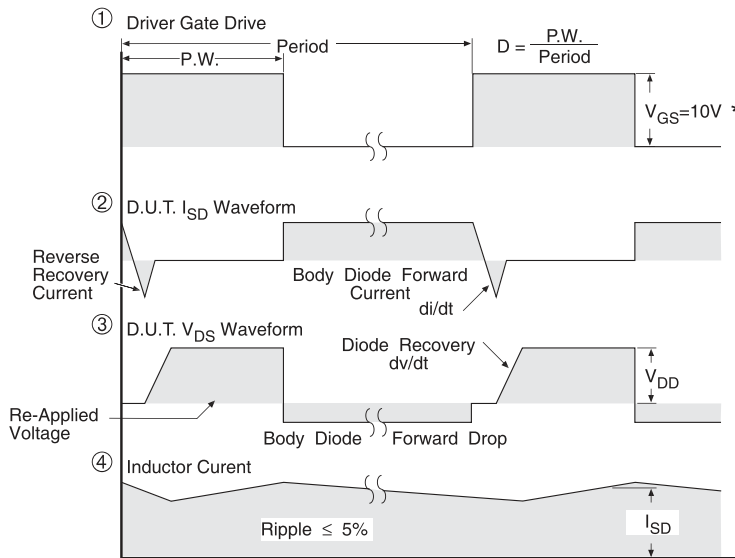
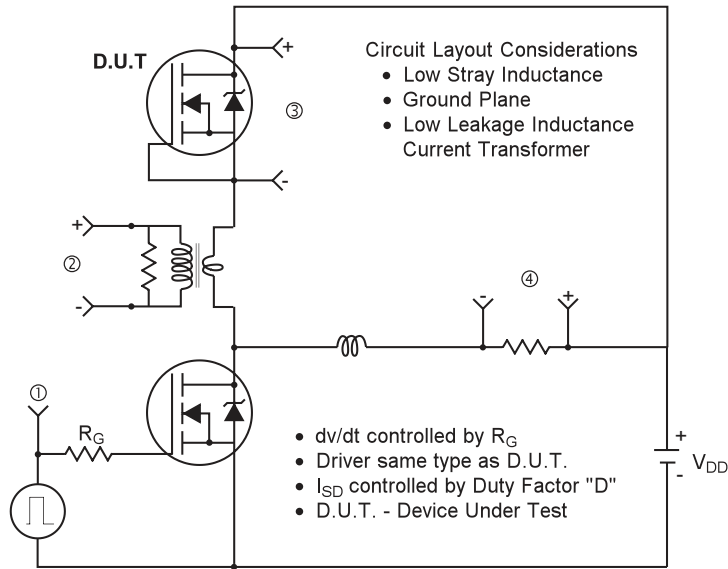


**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



\*  $V_{GS} = 5V$  for Logic Level Devices

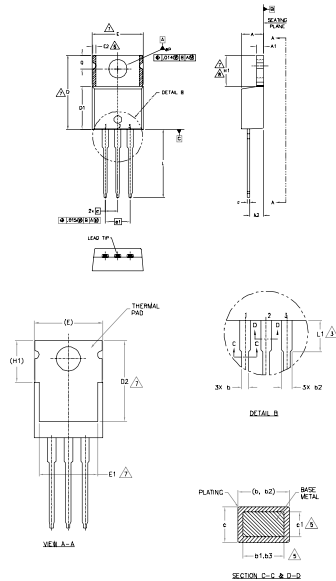
**Fig 14.** For N-Channel HEXFETS

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## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



- NOTES
- 1- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M-1994.
  - 2- DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS).
  - 3- LEAD DIMENSION AND FINISH UNCONTROLLED IN U.S.
  - 4- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .002" (0.075) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMITY OF THE PLASTIC BODY.
  - 5- DIMENSION H, H2 & H1 APPLY TO BASE METAL ONLY.
  - 6- CONTROLLING DIMENSION: INCHES.
  - 7- THERMAL PAD CONTOUR OPTIONAL. WITHIN DIMENSIONS E, H1, D2 & E1.
  - 8- DIMENSION E2 IS HI-ZERFEE & ZONE BINDER STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
  - 9- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D3 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.79	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	6.35	9.12	.250	.358	
D2	11.68	12.86	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54	3.05	.100	.120	
e1	2.54	3.05	.100	.120	
H	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	
HP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

LEAD ASSIGNMENT

- 1- GATE
- 2- CATHODE
- 3- ANODE

WIRE GAUGE

- 1- GATE
- 2- CATHODE
- 3- ANODE

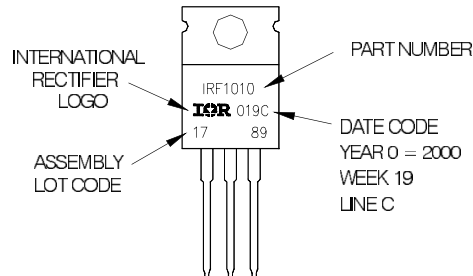
WIRE

- 1- PLATE
- 2- CATHODE
- 3- ANODE

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 2000  
 IN THE ASSEMBLY LINE 'C'

Note: 'P' in assembly line position indicates 'Lead-Free'



TO-220AB package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.



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